

INTRODUCE:

HVGT high voltage silicon rectifier assembly is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Power doubler circuit.
2. Power supply of laser equipment .
3. General purpose high voltage rectifier.
4. Other.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 7.2 grams (approx).

SHAPE DISPLAY:

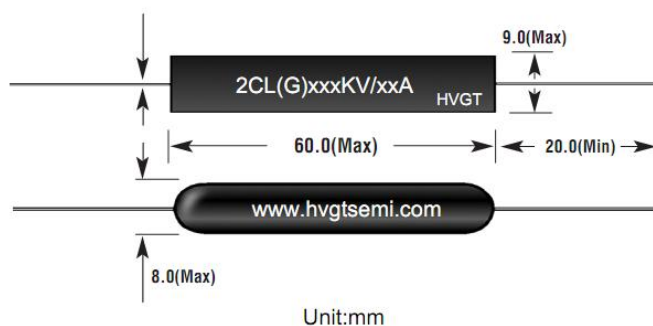


SIZE: (Unit:mm)

HVGT NAME: HVS-080960H

HVS-080960H Series

Lead Diameter 1.0mm



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	100	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=40^{\circ}C$	200	mA
Surge Current	I_{FSM}	$T_A=25^{\circ}C$; Half-Sine Wave; 8.3mS	6.0	A
Junction Temperature	T_J		125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$; at $I_{F(AV)}$	120	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--	pF



Fig 1

Forward Current Derating Curve

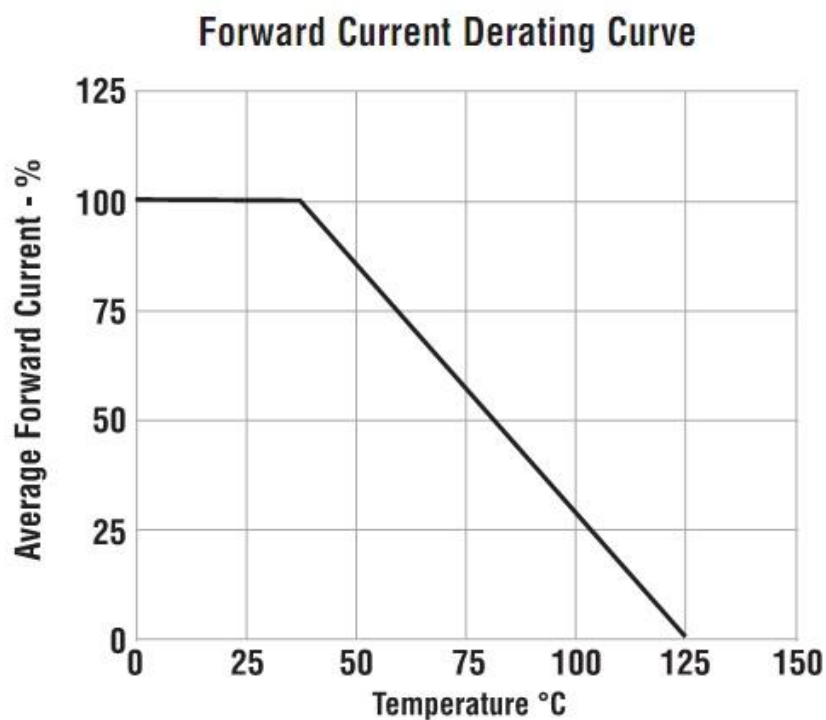


Fig 2

Non-Repetitive Surge Current

